

www.vishay.com

Vishay Semiconductors

# Thyristor High Voltage Surface Mount Phase Control SCR, 10 A



PRIMARY CHARACTERISTICS						
I <sub>T(AV)</sub>	6.5 A					
V <sub>DRM</sub> /V <sub>RRM</sub>	800 V					
$V_{TM}$	< 1.15 V					
I <sub>GT</sub>	15 mA					
TJ	-40 to +125 °C					
Package	D <sup>2</sup> PAK (TO-263AB)					
Circuit configuration	Single SCR					

#### **FEATURES**

- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- Designed and qualified according JEDEC®-JESD 47

 Material categorization: for definitions of compliance please see <a href="https://www.vishav.com/doc?99912">www.vishav.com/doc?99912</a>

### ROHS COMPLIANT HALOGEN FREE

#### **APPLICATIONS**

- Input rectification (soft start)
- Vishay input diodes, switches and output rectifiers which are available in identical package outlines

#### **DESCRIPTION**

The VS-10TTS08S-M3 high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS								
APPLICATIONS SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE UNITS								
NEMA FR-4 or G-10 glass fabric-based epoxy with 4 oz. (140 µm) copper	2.5	3.5						
Aluminum IMS, R <sub>thCA</sub> = 15 °C/W	6.3	9.5	A					
Aluminum IMS with heatsink, R <sub>thCA</sub> = 5 °C/W	14.0	18.5						

#### Note

•  $T_A = 55$  °C,  $T_J = 125$  °C, footprint 300 mm<sup>2</sup>

MAJOR RATINGS AND CHARACTERISTICS								
PARAMETER	TEST CONDITIONS	VALUES	UNITS					
I <sub>T(AV)</sub>	Sinusoidal waveform	6.5	۸					
I <sub>RMS</sub>		10	А					
V <sub>RRM</sub> /V <sub>DRM</sub>		800	V					
I <sub>TSM</sub>		110	A					
V <sub>T</sub>	6.5 A, T <sub>J</sub> = 25 °C	1.15	V					
dV/dt		150	V/µs					
dl/dt		100	A/µs					
T <sub>J</sub>	Range	-40 to +125	°C					

VOLTAGE RATINGS									
PART NUMBER	V <sub>RRM</sub> , MAXIMUM PEAK REVERSE VOLTAGE V	V <sub>DRM</sub> , MAXIMUM PEAK DIRECT VOLTAGE V	I <sub>RRM</sub> /I <sub>DRM</sub> AT 125 °C mA						
VS-10TTS08S-M3	800	800	1.0						





ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CO	TEST CONDITIONS				
Maximum average on-state current	I <sub>T(AV)</sub>	T 110 °C 100° conduc	tion half ains wave	6.5			
Maximum RMS on-state current	I <sub>T(RMS)</sub>	T <sub>C</sub> = 112 °C, 180° conduc	tion hall sine wave	10	Α		
Maximum peak, one-cycle,		10 ms sine pulse, rated V <sub>F</sub>	RRM applied, T <sub>J</sub> = 125 °C	95	А		
non-repetitive surge current	I <sub>TSM</sub>	10 ms sine pulse, no volta	ige reapplied, T <sub>J</sub> = 125 °C	110			
Marrian um 12t four frain a	I <sup>2</sup> t	10 ms sine pulse, rated V <sub>F</sub>	RRM applied, T <sub>J</sub> = 125 °C	45	A <sup>2</sup> s		
Maximum I <sup>2</sup> t for fusing	1-1	10 ms sine pulse, no volta	64	A <sup>2</sup> S			
Maximum I <sup>2</sup> √t for fusing	I²√t	t = 0.1 ms to 10 ms, no vo	Itage reapplied, $T_J = 125  ^{\circ}\text{C}$	640	A²√s		
Maximum on-state voltage drop	$V_{TM}$	6.5 A, T <sub>J</sub> = 25 °C	6.5 A, T <sub>J</sub> = 25 °C				
On-state slope resistance	r <sub>t</sub>	T 105.00		17.3	mΩ		
Threshold voltage	V <sub>T(TO)</sub>	T <sub>J</sub> = 125 °C		0.85	V		
Marries are recovered and direct leakage assures		T <sub>J</sub> = 25 °C	\/	0.05			
Maximum reverse and direct leakage current	I <sub>RM</sub> /I <sub>DM</sub>	T <sub>J</sub> = 125 °C	$V_R = \text{rated } V_{RRM} / V_{DRM}$	1.0			
Typical holding current	I <sub>H</sub>	Anode supply = 6 V, resist $T_J = 25 ^{\circ}\text{C}$	30	mA			
Maximum latching current	ΙL	Anode supply = 6 V, resist	50				
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J \text{ max., linear to } 80 \text{ %, } V_{DRM} = R_g - k = \text{open}$			V/µs		
Maximum rate of rise of turned-on current	dl/dt	100			A/μs		

TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum peak gate power	P <sub>GM</sub>		8.0	W	
Maximum average gate power	P <sub>G(AV)</sub>		2.0	VV	
Maximum peak positive gate current	+I <sub>GM</sub>		1.5	Α	
Maximum peak negative gate voltage	-V <sub>GM</sub>		10	V	
		Anode supply = 6 V, resistive load, T <sub>J</sub> = - 65 °C	20		
Maximum required DC gate current to trigger	$I_{GT}$	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	15	mA	
		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	10		
		Anode supply = 6 V, resistive load, T <sub>J</sub> = - 65 °C	1.2		
Maximum required DC gate voltage to trigger	$V_{GT}$	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	1	V	
voltage to trigger		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	0.7	V	
Maximum DC gate voltage not to trigger	$V_{GD}$	T = 105 °C V = reted value	0.2		
Maximum DC gate current not to trigger	$I_{GD}$	T <sub>J</sub> = 125 °C, V <sub>DRM</sub> = rated value	0.1	mA	

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Typical turn-on time	t <sub>gt</sub>	T <sub>J</sub> = 25 °C	0.8	
Typical reverse recovery time	t <sub>rr</sub>	T 105 °C	3	μs
Typical turn-off time	t <sub>q</sub>	T <sub>J</sub> = 125 °C	100	

### www.vishay.com

## Vishay Semiconductors

THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	VALUES	UNITS							
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-40 to +125	°C					
Maximum thermal resistance, junction to case	R <sub>thJC</sub>	DC operation	1.5	°C/W					
Typical thermal resistance, junction to ambient (PCB mount)			40	C/VV					
Approximate weight			2	g					
Approximate weight			0.07	oz.					
Marking device		Case style D <sup>2</sup> PAK (TO-263AB)	10TTS	08S					

#### Note

<sup>(1)</sup> When mounted on 1" square (650 mm²) PCB of FR-4 or G-10 material 4 oz. (140 μm) copper 40 °C/W. For recommended footprint and soldering techniques refer to application note #AN-994

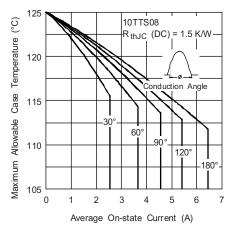


Fig. 1 - Current Rating Characteristics

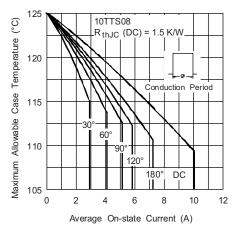


Fig. 2 - Current Rating Characteristics

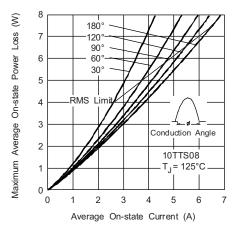


Fig. 3 - On-State Power Loss Characteristics

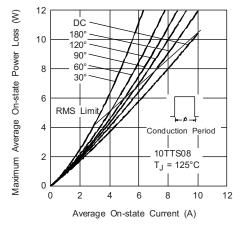


Fig. 4 - On-State Power Loss Characteristics

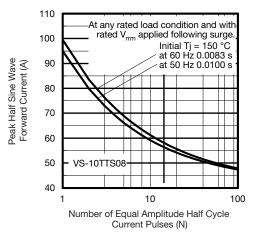


Fig. 5 - Maximum Non-Repetitive Surge Current

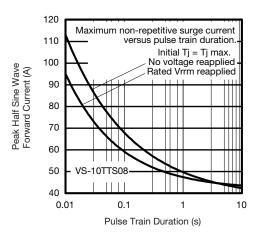


Fig. 6 - Maximum Non-Repetitive Surge Current

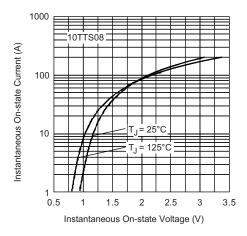


Fig. 7 - On-State Voltage Drop Characteristics

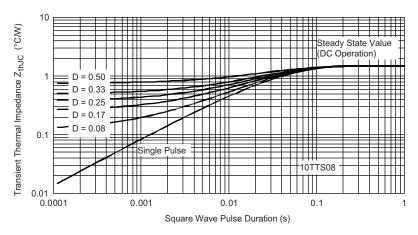
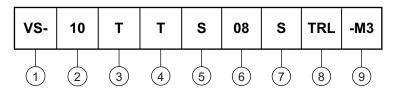


Fig. 8 - Thermal Impedance ZthJC Characteristics

### **ORDERING INFORMATION TABLE**

Device code



1 - Vishay Semiconductors product

Current rating, RMS value

Circuit configuration:

T = single thyristor

4 - Package:

 $T = D^2PAK (TO-263AB)$ 

5 - Type of silicon:

S = converter grade

Voltage code x 100 = V<sub>RRM</sub>

7 - S = surface mountable

8 - Tape and reel option:

• TRL = tape and reel (left oriented)

• TRR = tape and reel (right oriented)

9 - -M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)								
PREFERRED P/N BASE QUANTITY PACKAGING DESCRIPTION								
VS-10TTS08S-M3	50	Antistatic plastic tubes						
VS-10TTS08STRL-M3	800	13" diameter plastic tape and reel						
VS-10TTS08STRR-M3	800	13" diameter plastic tape and reel						

LINKS TO RELATED DOCUMENTS						
Dimensions <u>www.vishay.com/doc?96164</u>						
Part marking information	www.vishay.com/doc?95444					
Packaging information	www.vishay.com/doc?96424					



## D<sup>2</sup>PAK

#### **DIMENSIONS** in millimeters and inches



SYMBOL	MILLIM	ETERS	INC	HES	NOTES	NOTES	SYMBOL	MILLIM	ETERS	INC	HES	NOTES
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOIES		STINIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

#### Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inches
- (7) Outline conforms to JEDEC® outline TO-263AB

Revision: 13-Jul-17 Document Number: 96164



## **Legal Disclaimer Notice**

Vishay

### **Disclaimer**

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.